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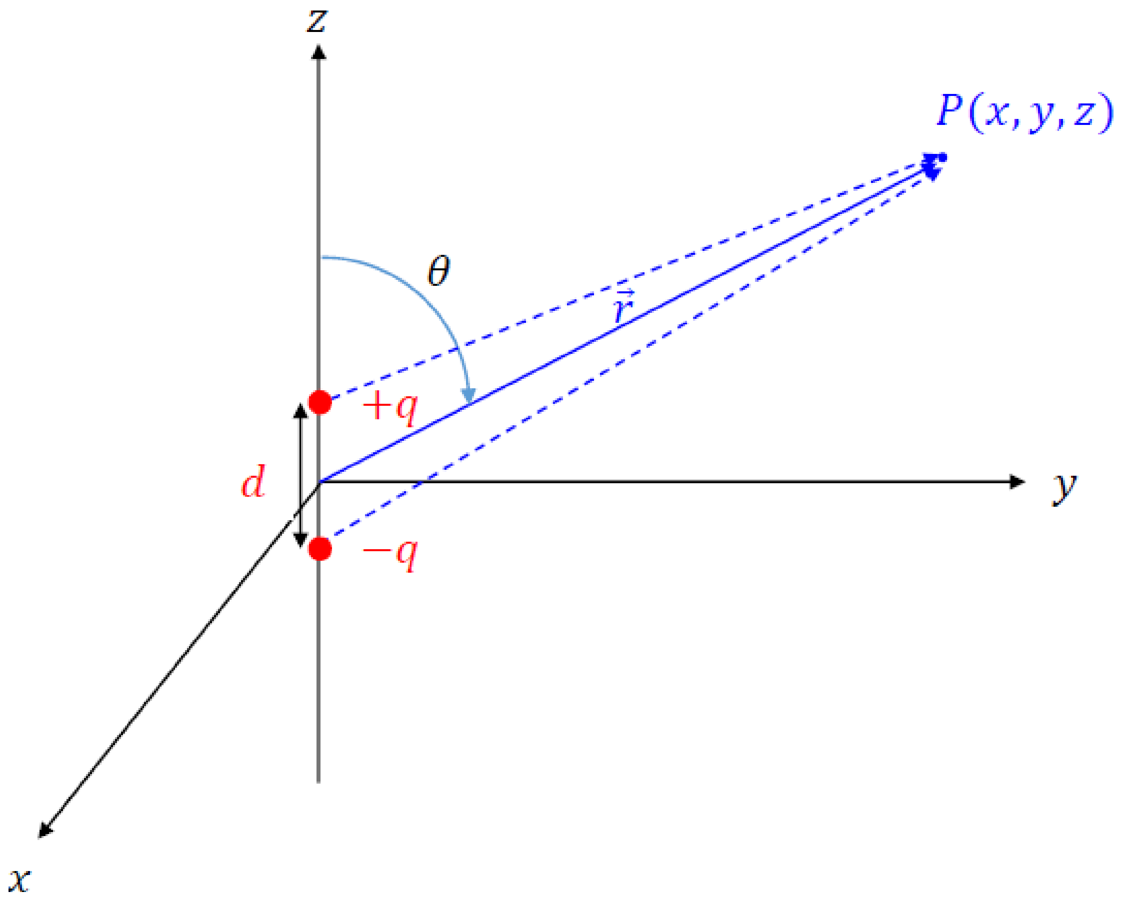
Electric Dipoles



$$V(P) = \frac{1}{4\pi\varepsilon_0}\left[\frac{q}{\sqrt{\left(z-\frac{d}{2}\right)^2+x^2+y^2}} - \frac{q}{\sqrt{\left(z+\frac{d}{2}\right)^2+x^2+y^2}}\right]$$

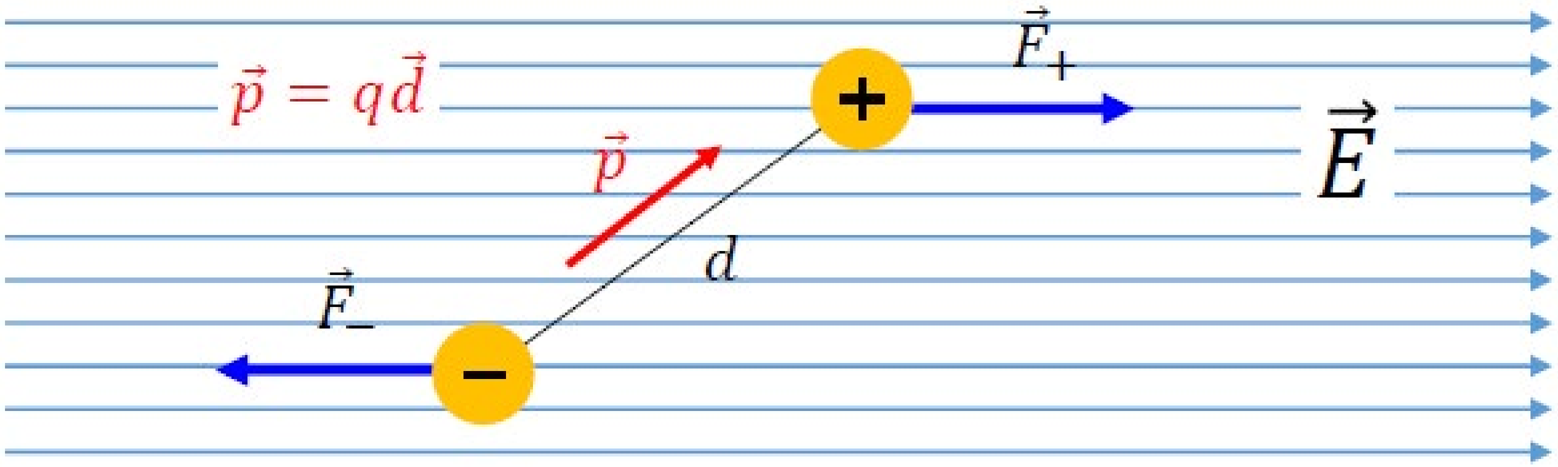
$$\boxed{V(P) = \frac{q}{4\pi\varepsilon_0}\frac{zd}{r^3}} \qquad \boxed{r >> d}$$

$$\vec{\boldsymbol{p}} = \boldsymbol{q}\vec{\boldsymbol{d}} \qquad \vec{\boldsymbol{p}} = \boldsymbol{\alpha_e}\vec{\boldsymbol{E}}_{\boldsymbol{loc}} \qquad [p] = \mathrm{Cm} \quad [\alpha_e] = \mathrm{F}m^2$$

$\boldsymbol{\alpha_e}$ = atomic (electronic) polarizability

$$V(\vec{r}) = \frac{\vec{p}.}{4\pi\varepsilon_0}\boxed{\frac{\vec{e}_r}{r^2}} = \frac{1}{4\pi\varepsilon_0}\vec{p}.\boxed{\vec{\nabla}\left(-\frac{1}{r}\right)}$$

Electric Dipoles



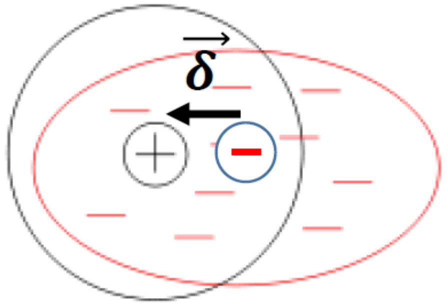
$$U = -pE\cos\theta = -\vec{p}.\vec{E}$$

$$\vec{E}_1 = \frac{1}{4\pi\varepsilon_0}\frac{1}{r^3}[3(\vec{p}_1.\vec{e}_r)\vec{e}_r - \vec{p}_1]$$

Dipole $\vec{p}_2$in field $\vec{E}_1$due to dipole $\vec{p}_1$

$$U = -\frac{1}{4\pi\varepsilon_0}\frac{1}{r^3}\vec{p}_2.[3(\vec{p}_1.\vec{e}_r)\vec{e}_r - \vec{p}_1]$$

Crude model: electronic polarization



Electronic cloud = charged sphere $E(r) = -\frac{1}{4\pi\varepsilon_0}\frac{Q}{R^3}r$

Force exerted on the nucleus (charge Q) inside the cloud at distance δ from the center $F_{cloud} = QE(\delta) = -\frac{1}{4\pi\varepsilon_0}\frac{Q^2}{R^3}\delta$

Equilibrium position is reached when $\vec{F}_{cloud} + \vec{F}_{ext} = \vec{0}$ ⇒ $-\frac{1}{4\pi\varepsilon_0}\frac{Q^2}{R^3}\delta + QE_{ext} = 0$

Equilibrium distance $\delta = 4\pi\varepsilon_0 R^3 \frac{E_{ext}}{Q}$

Induced dipole $\vec{\boldsymbol{p}} = \boldsymbol{Q}\vec{\boldsymbol{\delta}}$ $p = Q\delta = 4\pi\varepsilon_0 R^3 E_{ext}$

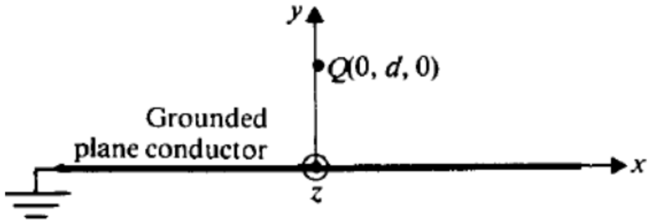
$\vec{p} = \alpha_e \vec{E}_{loc}$ $\vec{E}_{loc} = \vec{E}_{ext}$

Electronic polarizability of atoms

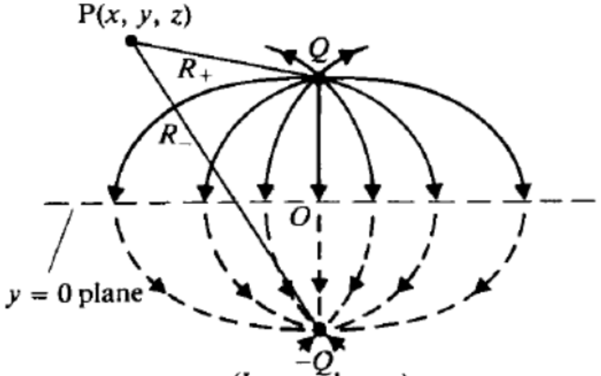
$$\boldsymbol{\alpha_e} = \frac{p}{E_{ext}} = 4\pi\varepsilon_0 R^3$$

Image Method

- Infinite Conducting Plane

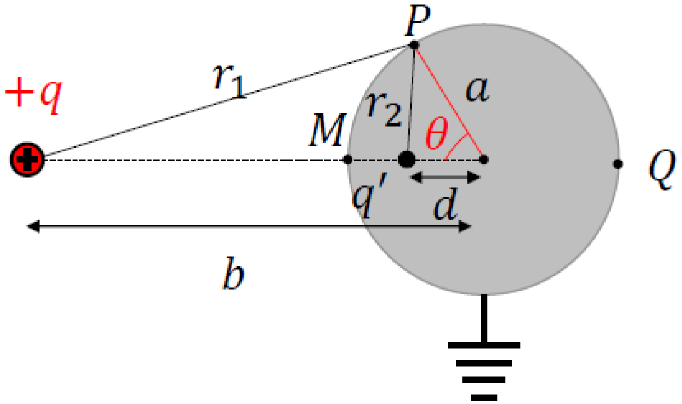


(a) Physical arrangement.



(b) Image charge and field lines.

- Conducting Sphere



$$V(M) = V(Q) = 0 \Rightarrow \begin{cases} d = \dfrac{a^2}{b} \\ q' = -\dfrac{a}{b} q \end{cases}$$

New Concepts

- Polarization
- Bound charges (linear, surface, volume)
- Permittivity of materials $\varepsilon = \varepsilon_0\varepsilon_r$ ($\varepsilon_r = 1$ in vacuum)
- Electric susceptibility χ ⇨ $\varepsilon = \varepsilon_0(1+\chi)$ ($\chi = 0$)
- Vector displacement $\vec{D}$

Dielectric

- A dielectric has the ability to get **polarized** by an **external** applied field
  ⇔ The applied external field <u>induces electric dipoles</u> inside the dielectric

- Polarization occurs in both **polar** and **nonpolar** materials

- Although any kind of substance is **polarizable** to some extent, the effect of <u>polarization is important only in dielectric materials</u>

- The dielectric is an insulator **BUT** an insulator is not necessarily a dielectric

Dielectric

- Polarized charge density on the surface

$$\boxed{\rho_{ps} = \mathbf{P} \cdot \mathbf{a}_n}$$

- Polarized charge density inside the dielectric

$$\boxed{\rho_p = -\nabla \cdot \mathbf{P}.}$$

- Electric displacement

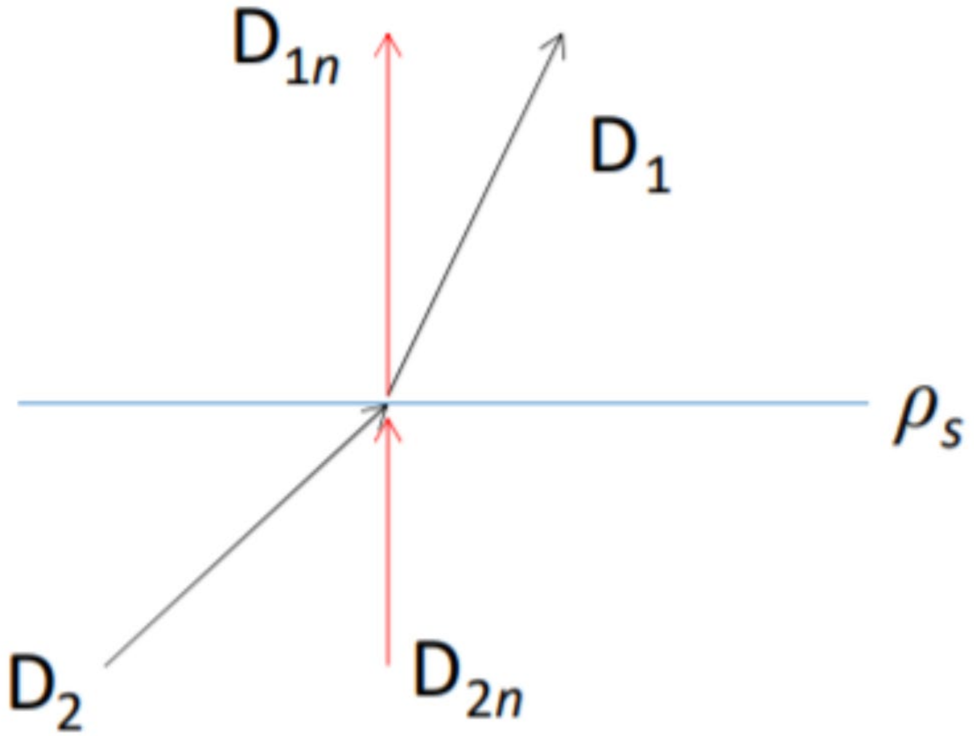
$$\boxed{\mathbf{D} = \epsilon_0 \mathbf{E} + \mathbf{P} \qquad (\mathrm{C/m^2}).}$$

$$\boxed{\nabla \cdot \mathbf{D} = \rho \qquad (\mathrm{C/m^3}),}$$

$$\boxed{\begin{aligned} \mathbf{D} &= \epsilon_0(1 + \chi_e)\mathbf{E} \\ &= \epsilon_0 \epsilon_r \mathbf{E} = \epsilon \mathbf{E} \qquad (\mathrm{C/m^2}), \end{aligned}}$$

Boundary Conditions for Electrostatic Fields

Tangential components,	$E_{1t} = E_{2t}$;
Normal components,	$\mathbf{a}_{n2} \cdot (\mathbf{D}_1 - \mathbf{D}_2) = \rho_s$.



$$D_{1n} - D_{2n} = \rho_s \quad (\mathrm{C/m^2})$$

Capacitor

- Capacitance: $$Q = CV$$

$$C = \frac{\varepsilon_r \varepsilon_0 A}{d}$$

Exercise 1

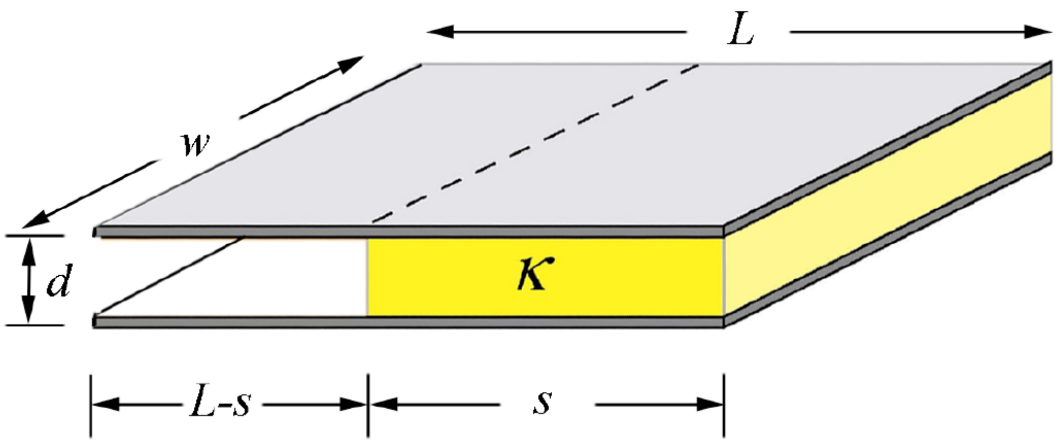
A layer of porcelain is 80 mm long, 20 mm wide and 0.7 µm thick. Calculate its capacitance with $\boldsymbol{\varepsilon_r}$ = 6

Exercise 2

The dielectric constant of a helium gas at NTP is 1.0000684. Calculate the electron polarizability of helium atoms if the gas contains 2.7×10^{26} atoms/m^3 and hence calculate the radius of helium atom ($\varepsilon_0 \;=\; 8.854 \;\times\; 10–12\ Fm^{-1}$)

Exercise 3

A dielectric rectangular slab has length s, width w, thickness d, and dielectric constant κ. The slab is inserted on the right hand side of a parallel-plate capacitor consisting of two conducting plates of width w, length L, and thickness d. The left hand side of the capacitor of length $L-s$ is empty. The capacitor is charged up such that the left hand side has surface charge densities $\pm\sigma_L$ on the facing surfaces of the top and bottom plates respectively and the right hand side has surface charge densities $\pm\sigma_R$ on the facing surfaces of the top and bottom plates respectively. The total charge on the entire top and bottom plates is $+Q$ and $-Q$ respectively. The charging battery is then removed from the circuit. ***Neglect all edge effects.***



Exercise 3

a) Find an expression for the magnitude of the electric field E_L on the left hand side in terms of σ_L, σ_R, κ, s, w, L, ε_0, and d as needed.

b) Find an expression for the magnitude of the electric field E_R on the right hand side in terms of σ_L, σ_R, κ, s, w, L, ε_0, and d as needed.

c) Find an expression that relates the surface charge densities σ_L and σ_R in terms of κ, s, w, L, ε_0, and d as needed.

d) What is the total charge $+Q$ on the entire top plate? Express your answer in terms of σ_L, σ_R, κ, s, w, L, ε_0, and d as needed.

e) What is the capacitance of this system? Express your answer in terms of κ, s, w, L, ε_0, and d as needed.

f) Suppose the dielectric is removed. What is the change in the stored potential energy of the capacitor? Express your answer in terms of Q, κ, s, w, L, ε_0, and d as needed.

Thank You

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